**Supporting information** 

## From liquid to thin film: colloidal suspensions for tungsten oxide as an electrode material for Li-ion batteries

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**Video S1**. Video footage of the synthesis performed.  $WCI_6$  was dissolved in Ethanol. After complete dissolution, water was added, shifting the color from yellow to colorless and finally dark blue.



**Figure S1**. MS data of headspace GCMS measurements performed on the precursors and ethanol, showing the 35.5-36.5 u fraction (HCl).



**Figure S2**. MS data of headspace GCMS measurements performed on the precursors and ethanol, showing the 102.5-1-3.5 u fraction (DEE).



**Figure S3**. TEM image of the tungsten precursor deposited on a copper grid and dried before measuring. The inset shows electron diffraction (ED) of a cluster of circular particles.



**Figure S4**. W4f XPS spectrum of WO<sub>3</sub> films annealed at 500°C for 1 hour (static air) on TiN. Etching times are indicates in seconds (s).



**Figure S5**. W4f XPS spectrum of WO<sub>3</sub> films annealed at 500°C for 1 hour (static air) on Pt. Etching times are indicates in seconds (*s*).



**Figure S6**. O1s XPS spectrum of  $WO_3$  films annealed at 500°C for 1 hour (static air) on TiN. Etching times are indicates in seconds (*s*).



**Figure S7**. O1s XPS spectrum of WO<sub>3</sub> films annealed at 500°C for 1 hour (static air) on Pt. Etching times are indicates in seconds (s).



**Figure S8**. Cl2p XPS spectrum of WO<sub>3</sub> films annealed at 500°C for 1 hour (static air) on TiN. Etching times are indicates in seconds (s).



**Figure S9**. Cl2p XPS spectrum of WO<sub>3</sub> films annealed at 500°C for 1 hour (static air) on Pt. Etching times are indicates in seconds (*s*).



**Figure S10**. Charge/discharge measurements of 10 layers of WO3 deposited on TiN (black) and Pt (red), measured at 1 mV·s-1 in 1.0 m LiClO<sub>4</sub> in PC. The films were submitted to a post deposition anneal of 1 hour at 400°C in static air.